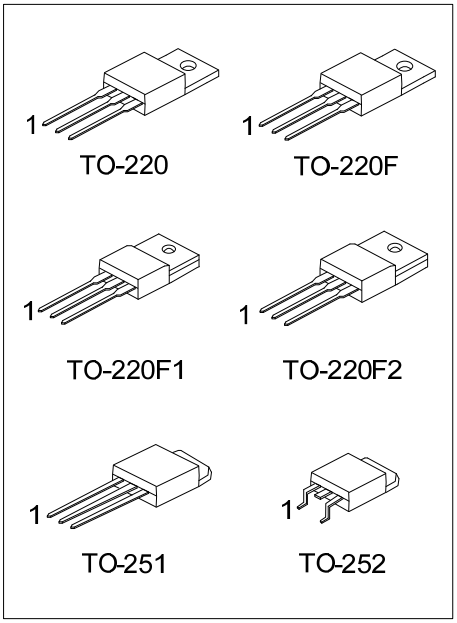
10N30

Power MOSFET

10A, 300V N-CHANNEL POWER MOSFET



■ DESCRIPTION

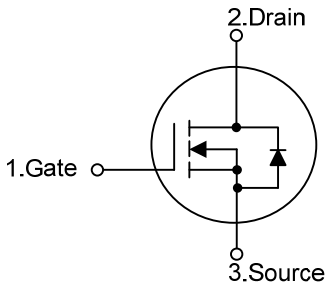
The UTC **10N30** is an N-channel mode power MOSFET using UTC' s advanced technology to provide customers with planar stripe and DMOS technology. This technology specializes in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **10N30** is universally applied in electronic lamp ballast based on half bridge topology and high efficient switched mode power supply.

■ FEATURES

* $R_{DS(ON)} \leq 0.4\ \Omega$ @ V_{GS}=10V, I_D=10A
* High switching speed
* 100% avalanche tested

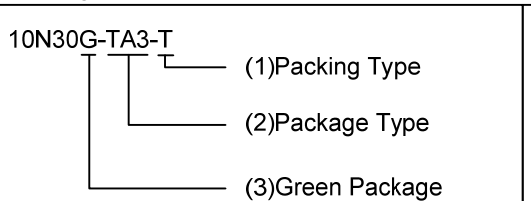
■ SYMBOL



■ ORDERING INFORMATION

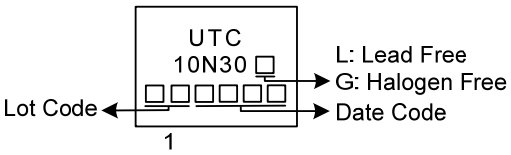
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10N30L-TA3-T	10N30G-TA3-T	TO-220	G	D	S	Tube
10N30L-TF1-T	10N30G-TF1-T	TO-220F1	G	D	S	Tube
10N30L-TF2-T	10N30G-TF2-T	TO-220F2	G	D	S	Tube
10N30L-TF3-T	10N30G-TF3-T	TO-220F	G	D	S	Tube
10N30L-TM3-T	10N30G-TM3-T	TO-251	G	D	S	Tube
10N30L-TN3-T	10N30G-TN3-T	TO-252	G	D	S	Tube
10N30L-TN3-R	10N30G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TM3: TO-251, TN3: TO-252
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	300	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous (T_C=25°C)	I_D	10	A
	Pulsed (Note 2)	I_{DM}	20	A
Avalanche Current (Note 2)		I_{AR}	11	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	314	mJ
	Repetitive (Note 4)	E_{AR}	13.5	mJ
Power Dissipation	TO-220	P_D	135	W
	TO-220F/TO-220F1 TO-220F2		32	
	TO-251/TO-252		83	
Derate above 25°C	TO-220		1.07	W/°C
	TO-220F/TO-220F1 TO-220F2		0.256	
	TO-251/TO-252		0.66	
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 5.7mH, I_{AS} = 10.5A, V_{DD} = 25V, R_G = 25Ω, Starting T_J = 25°C
4. I_{SD} ≤ 10.5A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2	θ_{JA}	62.5	°C/W
	TO-251/TO-252		110	°C/W
Junction to Case	TO-220	θ_{JC}	0.93	°C/W
	TO-220F/TO-220F1 TO-220F2		3.9	°C/W
	TO-251/TO-252		1.5 (Note)	°C/W

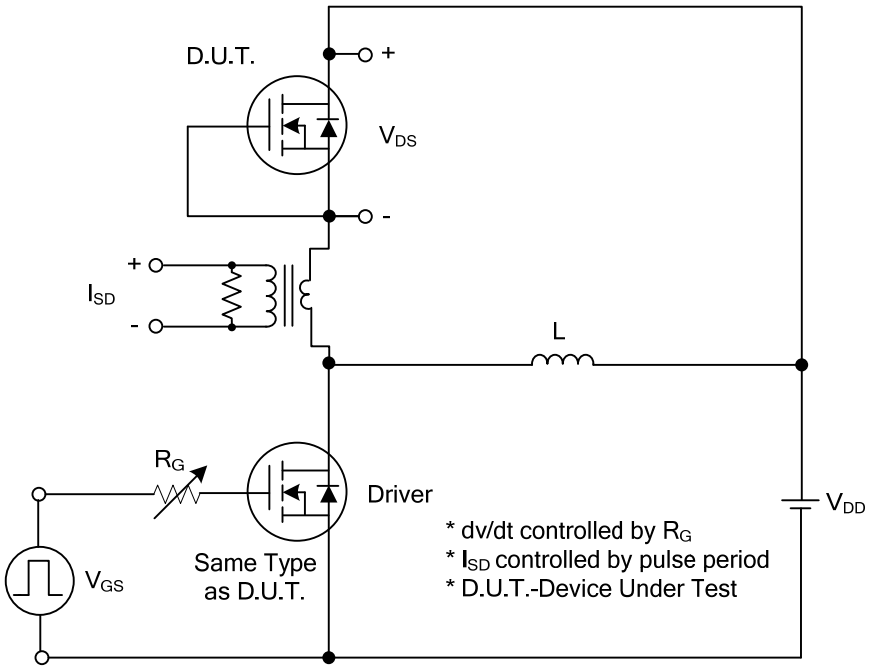
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

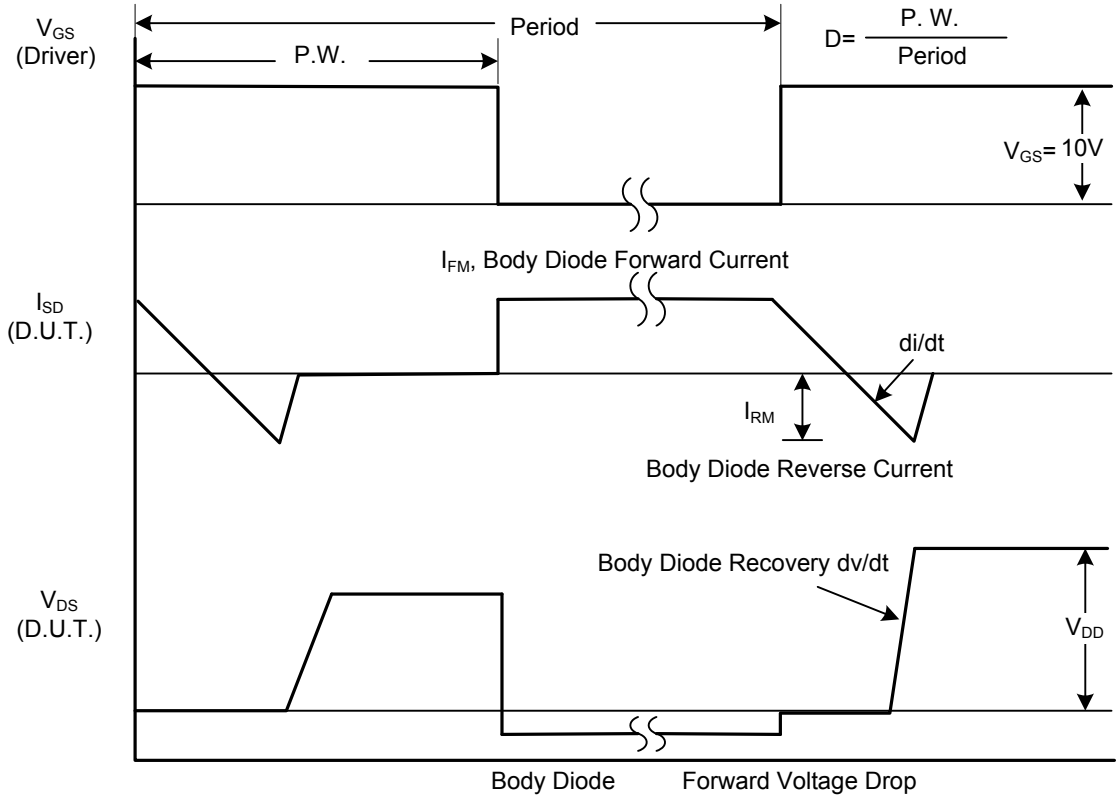
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	300			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=300V, V_{GS}=0V			1	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=10A			0.4	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		900		pF
Output Capacitance		C_{OSS}			140		pF
Reverse Transfer Capacitance		C_{RSS}			12		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{GS}=10V, V_{DS}=240V, I_D=10A (Note 1, 2)		23		nC
Gate to Source Charge		Q_{GS}			5.6		nC
Gate to Drain Charge		Q_{GD}			6		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D=10A, R_G=25Ω (Note 1, 2)		12		ns
Rise Time		t_R			19		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			53		ns
Fall-Time		t_F			22		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				10	A
Maximum Body-Diode Pulsed Current		I_{SM}				40	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=10A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t_{rr}	I_S=10A, V_{GS}=0V, dI_F/dt=100A/μs		218		nS
Body Diode Reverse Recovery Charge		Q_{rr}			3.88		μC

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

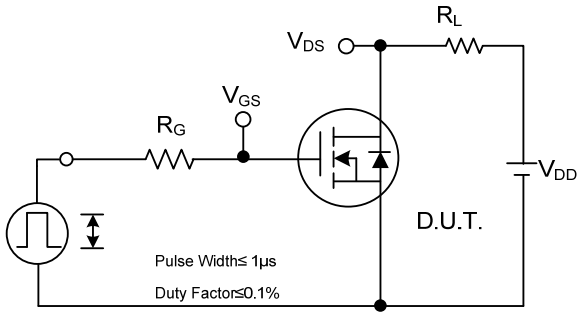


Peak Diode Recovery dv/dt Test Circuit

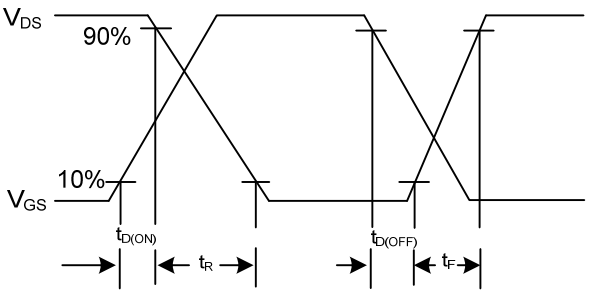


Peak Diode Recovery dv/dt Waveforms

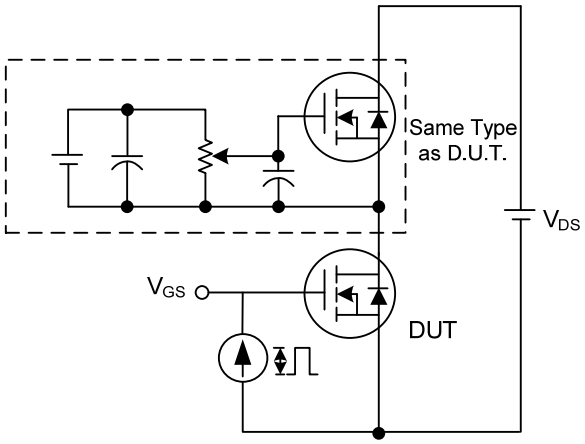
■ TEST CIRCUITS AND WAVEFORMS



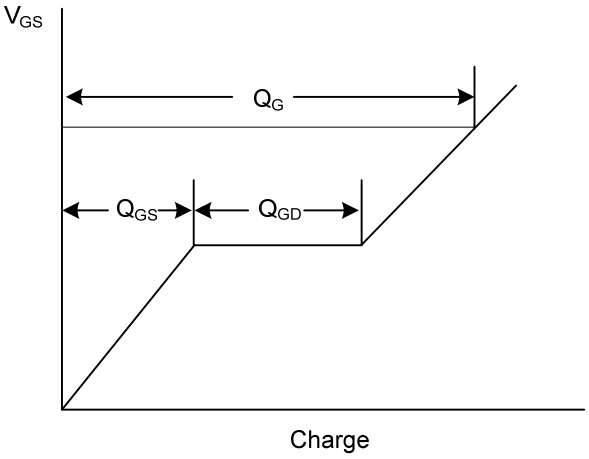
Switching Test Circuit



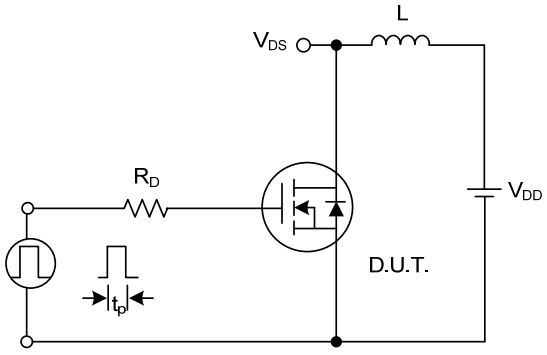
Switching Waveforms



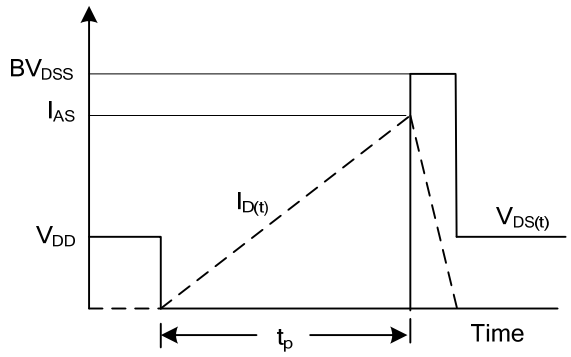
Gate Charge Test Circuit



Gate Charge Waveform



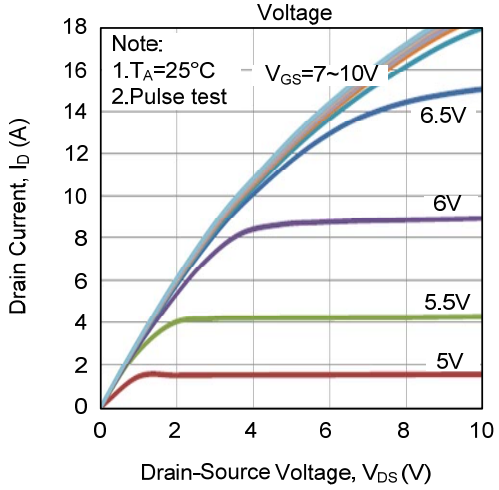
Unclamped Inductive Switching Test Circuit



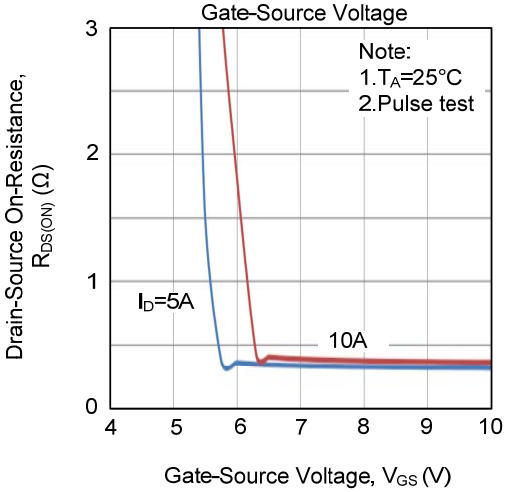
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

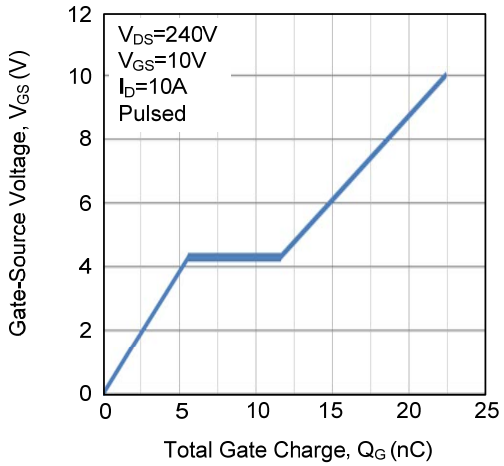
Drain Current vs. Drain-Source Voltage



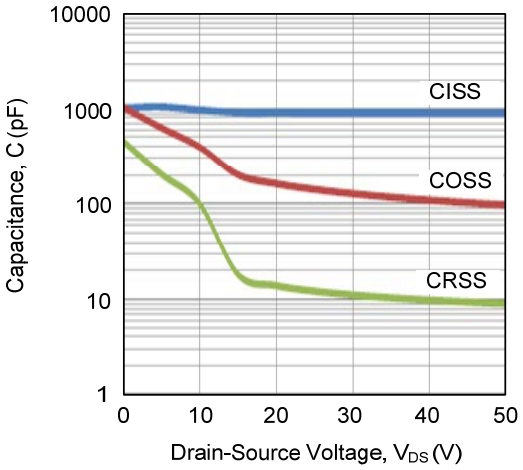
Drain-Source On-Resistance vs. Gate-Source Voltage



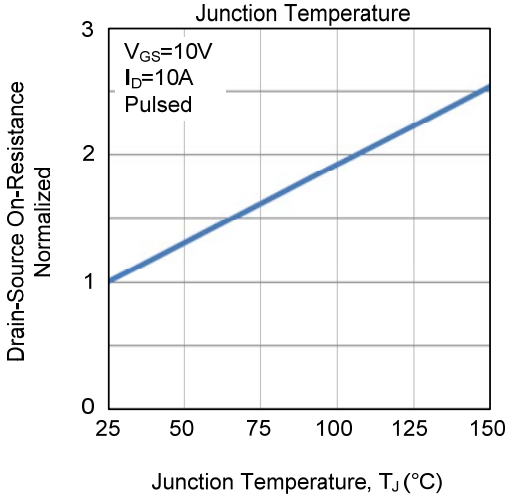
Gate Charge Characteristics



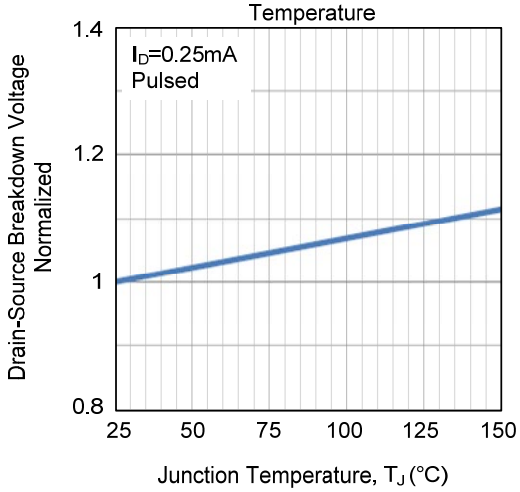
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

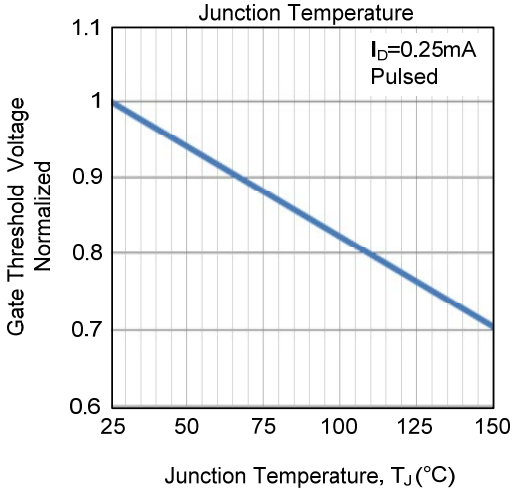


Breakdown Voltage vs. Junction Temperature

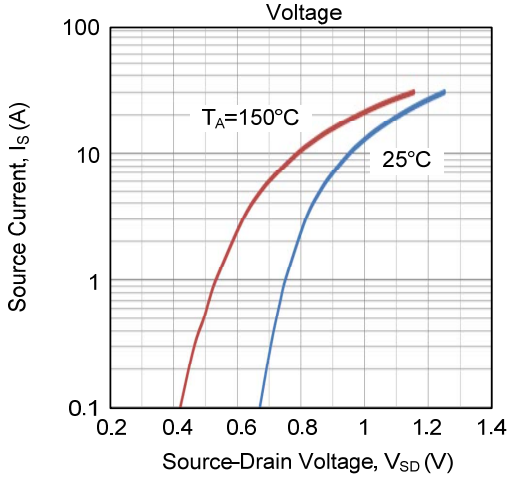


■ TYPICAL CHARACTERISTICS (Cont.)

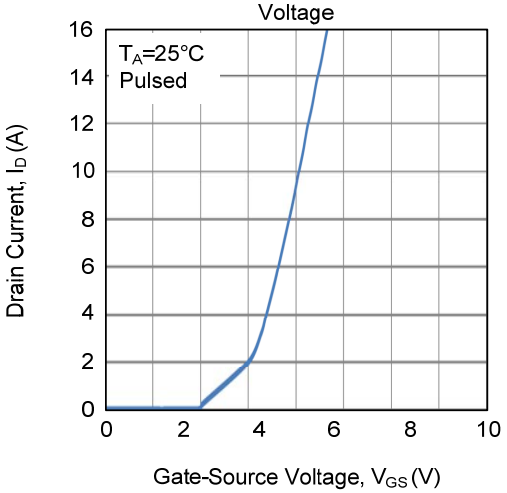
Gate Threshold Voltage vs. Junction Temperature



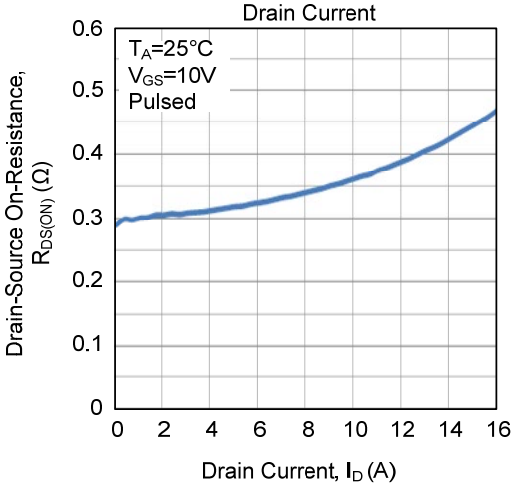
Source Current vs. Source-Drain Voltage



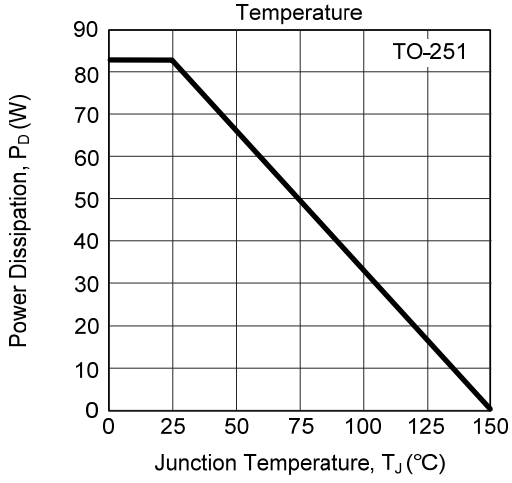
Drain Current vs. Gate-Source Voltage



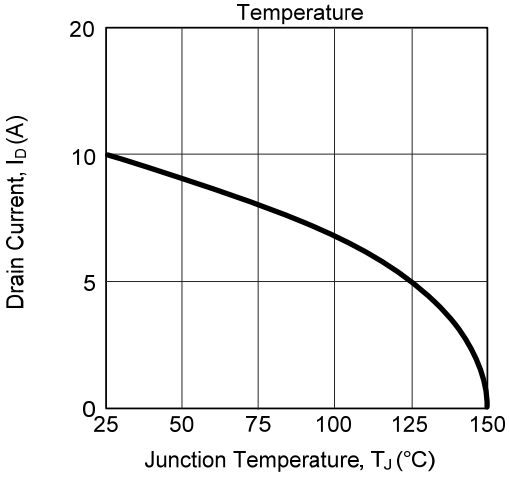
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)